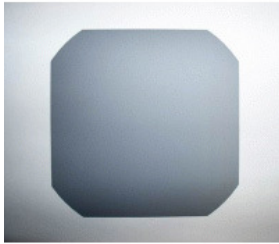




The Sustainable Way of Life.....

125mm x 125mm Monocrystalline Silicon Wafers Pseudo-Square CZ-Si Wafer Specifications

Technical Specifications

PV-W125MOM	
	
Crystal Type:	monocrystalline
Growth Method:	CZ
Ingot diameter	(150 +/-0,5)mm (Ingots must be surface ground).
Type	Dopant P / Boron
Orientation	(100)+/-3 degree
Resitivity:	0.5 – 3 Ohm*cm or 3-6 Ohm/cm
Carbon:	3×10^{16}atoms/cc
Oxygen:	1×10^{18}atoms/cc
Lifetime:	not less than 10 μ s
Average dislocation denty	cm-3: not more than 100
Parameters of Wafers	
Pseudosquare's side:	(125 x 125)+/-0,5mm
Side orientation	$\langle 100 \rangle$ +/- 3 degree
Life time:	≥ 10 usec
Corner between pseudosquare's side:	(90+/- 0,3) degree
Thickness of wafer, measured in the center of wafer:	(200 +/-30) μ m
TTV:	not more than 30 μ m
BOW:	less than 30 μ m
Edge chips	1 piece not longer than 1 mm not deeper than 0,8 mm